Sandrine Bernardini

List of Publications by Year in Descending Order

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Version: 2024-04-28

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

43	511 citations	12	21
papers		h-index	g-index
46	590	3.8 avg, IF	3.45
ext. papers	ext. citations		L-index

#	Paper	IF	Citations
43	BTEX gas sensor based on hematite microrhombuses. Sensors and Actuators B: Chemical, 2021, 326, 12	!8881.₹	6
42	Ammonia sensing properties of ZnO nanoparticles on flexible substrate. <i>International Journal on Smart Sensing and Intelligent Systems</i> , 2020 , 7, 1-4	0.4	1
41	Light-induced high-spin state in ZnO nanoparticles. <i>Nanotechnology</i> , 2020 , 31, 095707	3.4	2
40	Trends in metal oxide thin films: Synthesis and applications of tin oxide 2020 , 219-246		3
39	Highly selective ozone gas sensor based on nanocrystalline Zn0.95Co0.05O thin film obtained via spray pyrolysis technique. <i>Applied Surface Science</i> , 2019 , 478, 347-354	6.7	28
38	One-Dimensional V2O5/TiO2 Heterostructures for Chemiresistive Ozone Sensors. <i>ACS Applied Nano Materials</i> , 2019 , 2, 4756-4764	5.6	28
37	Efficiency of new ozone filters for NO2 sensing and air depollution. <i>Sensors and Actuators B: Chemical</i> , 2018 , 265, 591-599	8.5	7
36	Ammonia Detection at Low Temperature by Tungsten Oxide Nanowires. <i>Proceedings (mdpi)</i> , 2018 , 2, 983	0.3	1
35	Silver Growth on Tungsten Oxide Nanowires for Nitrogen Dioxide Sensing at Low Temperature. <i>Proceedings (mdpi)</i> , 2018 , 2, 946	0.3	
34	UV-enhanced ozone gas sensing response of ZnO-SnO2 heterojunctions at room temperature. <i>Sensors and Actuators B: Chemical</i> , 2017 , 240, 573-579	8.5	80
33	Selective Detection of NO2 with Specific Filters for O3 Trapping. <i>Proceedings (mdpi)</i> , 2017 , 1, 405	0.3	1
32	ZnO/SnO2 Heterojunctions Sensors with UV-Enhanced Gas-Sensing Properties at Room Temperature. <i>Proceedings (mdpi)</i> , 2017 , 1, 418	0.3	4
31	Ozone Sensors Working at Room Temperature Using Zinc Oxide Nanocrystals Annealed at Low Temperature. <i>Proceedings (mdpi)</i> , 2017 , 1, 423	0.3	3
30	Te implantation in Ge(001) for n-type doping applications. <i>Materials Science in Semiconductor Processing</i> , 2016 , 42, 215-218	4.3	1
29	Local Structure and Surface Properties of CoZnO Thin Films for Ozone Gas Sensing. <i>ACS Applied Materials & Sensing Sen</i>	9.5	45
28	Formation of germanium oxide microcrystals on the surface of Te-implanted Ge. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2015 , 365, 252-255	1.2	
27	Ozone and nitrogen dioxide gas sensor based on a nanostructured SrTi0.85Fe0.15O3 thin film. <i>Journal of Alloys and Compounds</i> , 2015 , 638, 374-379	5.7	37

26	Nanoporous Ge thin film production combining Ge sputtering and dopant implantation. <i>Beilstein Journal of Nanotechnology</i> , 2015 , 6, 336-42	3	4
25	An easy method of preparing ozone gas sensors based on ZnO nanorods. <i>RSC Advances</i> , 2015 , 5, 19528	-1 9 533	58
24	Ozone flexible sensors fabricated by photolithography and laser ablation processes based on ZnO nanoparticles. <i>Sensors and Actuators B: Chemical</i> , 2014 , 203, 602-611	8.5	50
23	Ammonia detection by a novel Pyrex microsystem based on thermal creep phenomenon. <i>Sensors and Actuators B: Chemical</i> , 2014 , 192, 714-719	8.5	7
22	Ozone Sensor on Flexible Substrate by ZnO Nanoparticles. <i>Key Engineering Materials</i> , 2014 , 605, 163-16	56 0.4	3
21	Direct Laser Patterning of a Gas Sensor on Flexible Substrate. <i>Procedia Engineering</i> , 2014 , 87, 899-902		2
20	Microfluidic gas sensor with integrated pumping system. <i>Sensors and Actuators B: Chemical</i> , 2012 , 170, 45-50	8.5	13
19	A New Active Organic Component for Flexible Ammonia Gas Sensors. <i>Procedia Engineering</i> , 2011 , 25, 1069-1072		3
18	Fabrication and characterization of gas detection microfluidic system. <i>Procedia Engineering</i> , 2010 , 5, 11	88-119	912
17	All solution processed flexible ammonia gas and light sensors based on	_	T.4
	Thexyl-distyrylbithiophene films. Sensors and Actuators B: Chemical, 2010, 151, 77-82	8.5	14
16	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104	3.4	23
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16	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104 Reliability degradation of thin HfO2/SiO2 gate stacks by remote RF hydrogen and deuterium	3.4	23
16 15	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104 Reliability degradation of thin HfO2/SiO2 gate stacks by remote RF hydrogen and deuterium plasma treatment. <i>Thin Solid Films</i> , 2008 , 517, 207-208 Nanoscale electrical characterization of ultrathin high-k dielectric MOS stacks: A conducting AFM	3·4 2.2 4·3	23
16 15 14	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104 Reliability degradation of thin HfO2/SiO2 gate stacks by remote RF hydrogen and deuterium plasma treatment. <i>Thin Solid Films</i> , 2008 , 517, 207-208 Nanoscale electrical characterization of ultrathin high-k dielectric MOS stacks: A conducting AFM study. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 250-253	3·4 2.2 4·3	23 7 3
16 15 14	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104 Reliability degradation of thin HfO2/SiO2 gate stacks by remote RF hydrogen and deuterium plasma treatment. <i>Thin Solid Films</i> , 2008 , 517, 207-208 Nanoscale electrical characterization of ultrathin high-k dielectric MOS stacks: A conducting AFM study. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 250-253 Chemical and optical profiling of ultra thin high-k dielectrics on silicon. <i>Thin Solid Films</i> , 2008 , 517, 459-6 Electrically active defects induced by hydrogen and helium implantations in Ge. <i>Materials Science in</i>	3·4 2.2 4·3 4612	23 7 3
16 15 14 13 12	Energy state distributions of the Pb centers at the (100), (110), and (111) SiBiO2 interfaces investigated by Laplace deep level transient spectroscopy. <i>Applied Physics Letters</i> , 2008 , 92, 242104 Reliability degradation of thin HfO2/SiO2 gate stacks by remote RF hydrogen and deuterium plasma treatment. <i>Thin Solid Films</i> , 2008 , 517, 207-208 Nanoscale electrical characterization of ultrathin high-k dielectric MOS stacks: A conducting AFM study. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 250-253 Chemical and optical profiling of ultra thin high-k dielectrics on silicon. <i>Thin Solid Films</i> , 2008 , 517, 459-459. Electrically active defects induced by hydrogen and helium implantations in Ge. <i>Materials Science in Semiconductor Processing</i> , 2008 , 11, 354-359 Extrinsic stacking fault generation related to high dielectric growth on a Si substrate.	3·4 2.2 4·3 4·61 ₂	23 7 3

8	The impact of negative-bias-temperature-instability on the carrier generation lifetime of metal-oxynitride-silicon capacitors. <i>Journal of Applied Physics</i> , 2006 , 100, 124103	2.5	21
7	. IEEE Nanotechnology Magazine, 2005 , 4, 360-368	2.6	19
6	Effect of fixed dielectric charges on tunnelling transparency in MIM and MIS structures. <i>Microelectronic Engineering</i> , 2004 , 72, 90-95	2.5	1
5	DC and AC MOS transistor modelling in presence of high gate leakage and experimental validation. <i>Solid-State Electronics</i> , 2004 , 48, 597-608	1.7	2
4	Origin and repartition of the oxide fixed charges generated by electrical stress in memory tunnel oxide. <i>Applied Physics Letters</i> , 2004 , 84, 4251-4253	3.4	1
3	Study of trap centres in silicon nanocrystal memories. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 102, 99-107	3.1	6
2	A new floating gate compact model applied to flash memory cell. <i>Journal of Non-Crystalline Solids</i> , 2003 , 322, 250-255	3.9	5
1	A tunneling model for gate oxide failure in deep sub-micron technology		1